

**Giant and reversible photoluminescence modulation based on *in situ*
electric-field-controlled antiferroelectric-ferroelectric phase
transition**

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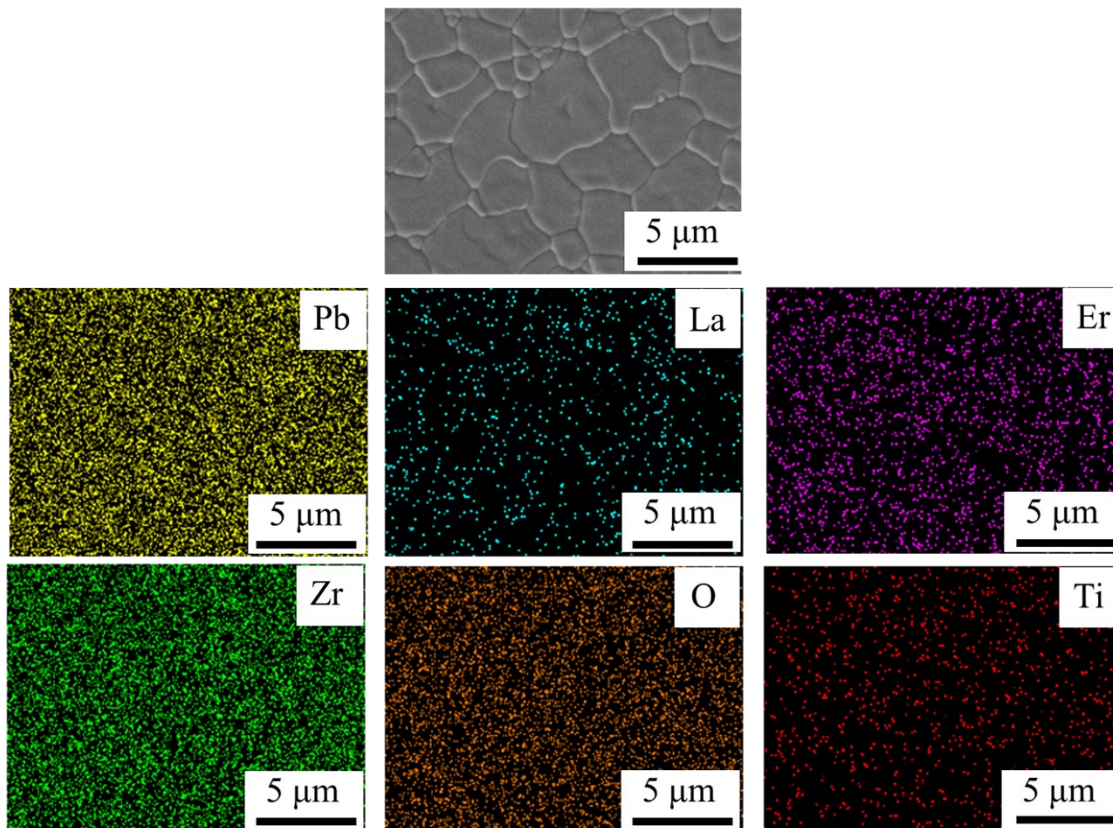


Figure S1. Scanning electron microscopy (SEM) image of the 0.5 mol% Er^{3+} doped $\text{Pb}_{0.96}\text{La}_{0.04}\text{Zr}_{0.9}\text{Ti}_{0.1}\text{O}_3$ (PLZT-Er) ceramic, and corresponding energy-dispersive X-ray spectroscopy (EDS) images that demonstrate the homogeneity of the elemental distribution.

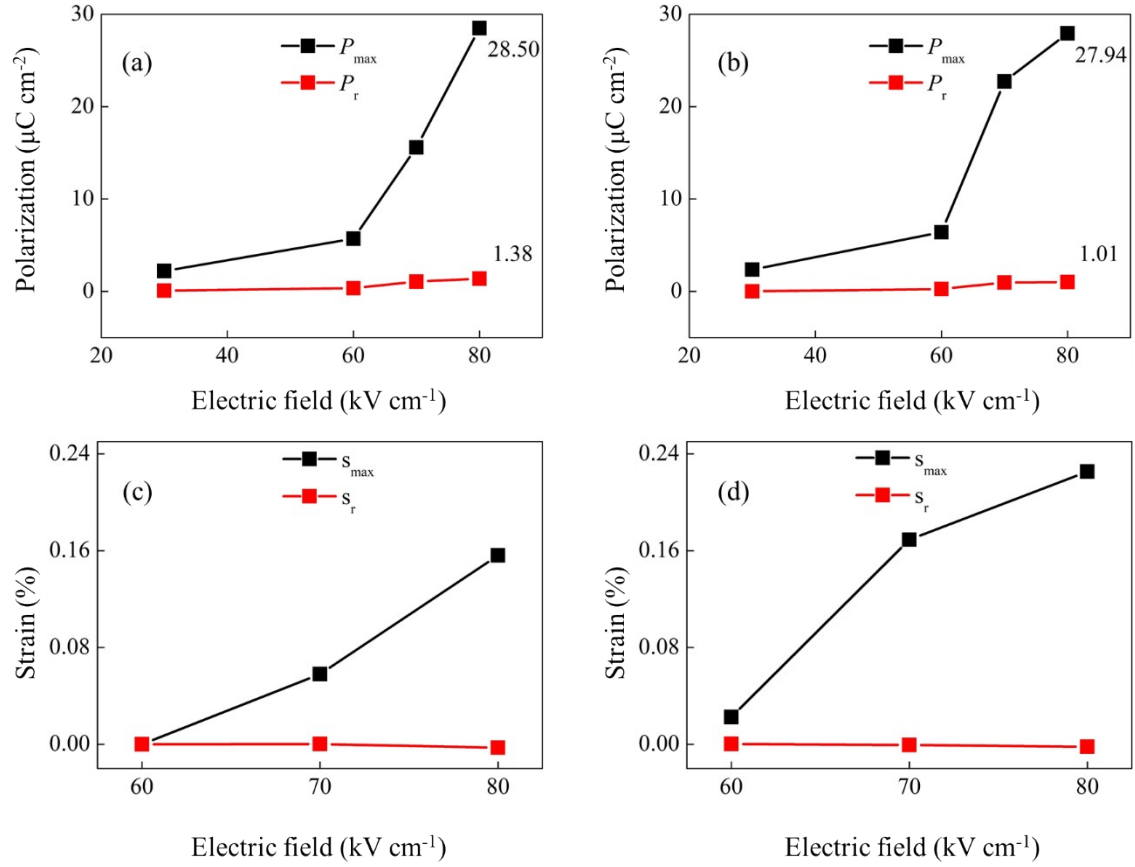


Figure S2. (a) (b) Maximum polarization (P_{max}) and remnant polarization (P_{r}) of PLZT and PLZT-Er under various maximum electric fields (E). (c) (d) Maximum strain (s_{max}) and remnant strain (s_{r}) of PLZT and PLZT-Er under various maximum electric fields (E). (a) (c) Pure PLZT, and (b) (d) PLZT-Er.

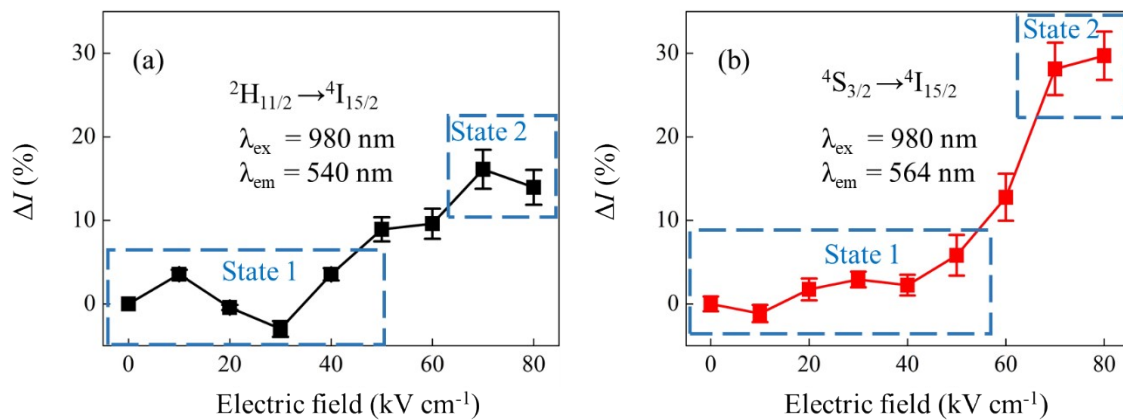


Figure S3. Photoluminescence (PL) enhancement ratio as a function of applying E from 0 to 80 kV cm⁻¹: (a) 540 nm, and (b) 564 nm. Two distinguishable states are marked.

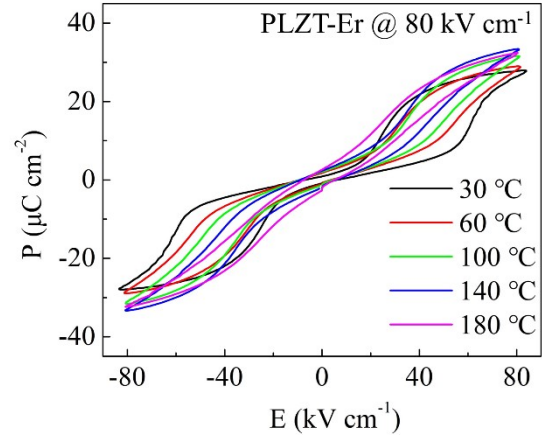


Figure S4. Temperature dependent P - E curves of PLZT-Er sample at $E = 80 \text{ kV cm}^{-1}$.

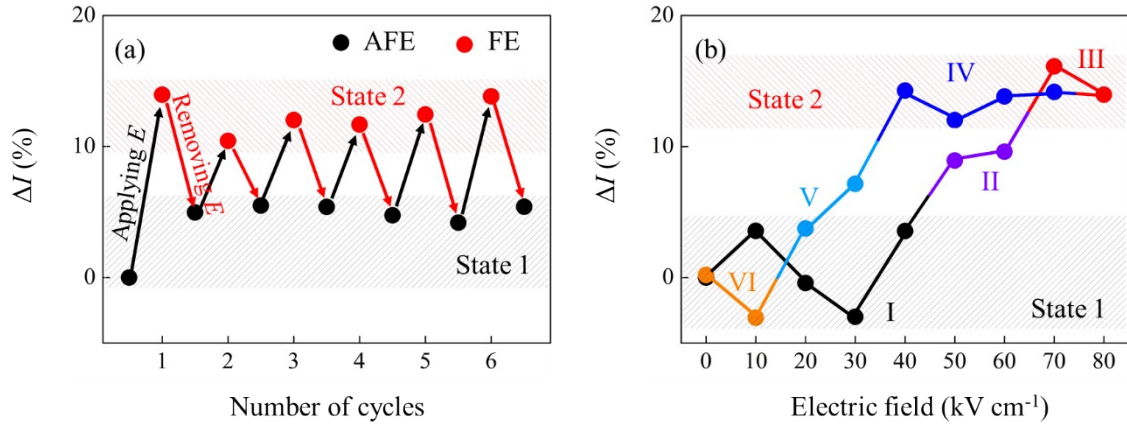


Figure S5. (a) PL enhancement ratio of PLZT-Er under an alternate E between 0 and 80 kV cm^{-1} . (b) PL enhancement ratio of the PLZT-Er ceramic under a cycle of *in situ* E between 0 and 80 kV cm^{-1} . Six nonlinear change sections (I to VI) and two distinguishable PL states are marked in (b). The PL band is at 540 nm.